

# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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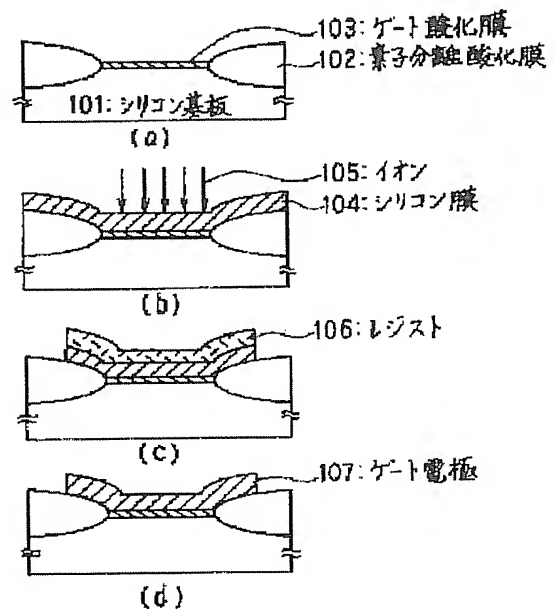
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APPLICANT : HITACHI LTD;

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TITLE : SEMICONDUCTOR DEVICE AND  
MANUFACTURE THEREOF



ABSTRACT : PURPOSE: To provide a semiconductor device in which boundary characteristics between a gate insulating film and a silicon substrate are improved without decreasing a capacity of a gate oxide film, without increasing a thickness of an insulating film and without deterioration of insulation of a MOS transistor and a MOS capacitor, etc.

CONSTITUTION: A semiconductor device comprises a silicon substrate 101, a gate oxide film 103 formed on the substrate, and a gate electrode 106 formed on the film 103 in such a manner that nitrogen atoms are doped in at least one of the substrate 101 and the electrode 106 and the film 103.

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